Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3769	250/207.ccls. 250/214VT.ccls. 250/214.1.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 10:53
L2	171	348/216.1.ccls. 348/217.1.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 10:53
L3	. 777	313/103CM.ccls. 313/105CM.ccls. 313/105R.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 10:53
L4	349808	"257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 10:53
L5	254207	(gap or distance) near5 (intensif\$9 or detect\$5 or imag\$5 or sens\$5 or gain\$5 or photodetect\$5 or photosens\$5 or CCD or CMOS)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 10:58
L6	281527	silicon near5 (die or substrate or member)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON .	2006/08/23 10:58
L7	113784	bond\$5 near5 (electrode or pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 10:58
L8	33806	(imag\$5 or electron\$5) near5 (intensif\$5 or gain)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 10:58
L9	767317 <sup>°</sup>	(notch\$2 or diced or step\$4) near5 (portion or end or substrate or member or die)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 10:59
L10	30180	5 and 9	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 10:59
L11	811	10 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 11:00

L12	6	1 and 11	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 11:00
L13	1	2 and 11	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 11:01
L14	2	3 and 11	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 11:01
L15	63	4 and 11	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 11:02

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	3769	250/207.ccls. 250/214VT.ccls. 250/214.1.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:29
L3	171	348/216.1.ccls. 348/217.1.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:29
L4	777	313/103CM.ccls. 313/105CM.ccls. 313/105R.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:29
L5	349808	"257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:29
L6	254207	(gap or distance) near5 (intensif\$9 or detect\$5 or imag\$5 or sens\$5 or gain\$5 or photodetect\$5 or photosens\$5 or CCD or CMOS)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:32
L7	281527	silicon near5 (die or substrate or member)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:29
L8	113784	bond\$5 near5 (electrode or pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:29
L9	767317	(notch\$2 or diced or step\$4) near5 (portion or end or substrate or member or die)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:29
L10	337375	(gap or distance) near5 (IC or integrat\$5 or circuit or board or member or die or substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:36
L11	19809	7 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:36
L12	4511	10 and 11	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:36

L13	12	2 and 12	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:38
L14	0	3 and 12	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:36
L15	0	4 and 12	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:36
L16	2437	5 and 12	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:36
L17	1277	16 and 9	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:39
L18	3514	array near5 8	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:39
L19	138	17 and 18	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/23 13:39